ABSTRACT

NITRIDING METHOD FOR INSULATION FILM, SEMICONDUCTOR DEVICE AND PRODUCTION METHOD FOR SEMICONDUCTOR DEVICE, SUBSTRATE TREATING DEVICE AND SUBSTRATE TREATING METHOD

A method of nitriding an insulation film includes the steps of forming nitrogen radicals by high-frequency plasma, and causing nitridation in a surface of an insulation film containing therein oxygen, by supplying the nitrogen radicals to the surface of the insulation film.

Refer to Figures 1 and 41A